

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A lithographic apparatus, comprising:
 - a radiation source configured to provide radiation to an illumination system, the radiation source configured to provide radiation in a first wavelength range and in a second wavelength range, the second wavelength range being different from the first wavelength range;
 - a support configured to support a patterning device, the patterning device configured to impart the radiation with a pattern in its cross-section;
 - a substrate table configured to hold a substrate;
 - a projection system configured to project the patterned radiation onto a target portion of the substrate.
2. (Original) A lithographic apparatus according to claim 1, wherein the radiation source further comprises a radiation source capable of providing radiation in both the first and second wavelength range, and a removable filter configured to provide the radiation in the first or second wavelength range
3. (Original) A lithographic apparatus according to claim 1, wherein the radiation source further comprises a first radiation source element configured to provide radiation in the first wavelength range, and a second radiation source element configured to provide radiation in the second wavelength range, and a removable radiation director configured to direct radiation from the second radiation source element to the illumination system.
4. (Original) A lithographic apparatus according to claim 1, wherein the first wavelength range is a wavelength range used in a controlled environment, and the second wavelength range is a wavelength range used when the controlled environment is not established.
5. (Original) A lithographic apparatus according to claim 1, wherein the first wavelength range is in an EUV region.

6. (Original) A lithographic apparatus according to claim 5, wherein the first wavelength is about 13 nm.
7. (Original) A lithographic apparatus according to claim 1, wherein the first wavelength range is in a UV region.
8. (Original) A lithographic apparatus according to claim 7, wherein the first wavelength is in a region between about 157 nm to 193 nm.
9. (Currently Amended) A lithographic apparatus according to claim 1, wherein the second wavelength range is used for setup of the lithographic apparatus, the setup comprising ~~one or more of calibration, qualification, performance test, and alignment~~ (i) calibration, or (ii) qualification, or (iii) performance test, or (iv) alignment, or (v) any combination of (i)-(iv).
10. (Original) A lithographic apparatus according to claim 1, wherein the substrate is exposed using the first wavelength range, and the second wavelength range is used for exposure of a further substrate.
11. (Currently Amended) A lithographic apparatus according to claim ~~5~~⁴, wherein the second wavelength range is in a region between about 150 and 350 nm.
12. (Previously Presented) A device manufacturing method, comprising:
providing radiation at a first wavelength range and at a second wavelength range, the second wavelength range being different from the first wavelength range; and
patterning the radiation in its cross-section; and
projecting the patterned radiation onto a target portion of a substrate.
13. (Original) A method according to claim 12, further comprising filtering out radiation in the first or second wavelength range.

14. (Currently Amended) A method according to claim 12, further comprising directing radiation in the first or second wavelength range to ~~the~~an illumination system.
15. (Original) A method according to claim 12, wherein the first wavelength range is a wavelength range in which radiation propagates in a controlled environment, and the second wavelength range is a wavelength range in which radiation propagates when the controlled environment is not established.
16. (Original) A method according to claim 12, wherein the first wavelength range is in an EUV region.
17. (Original) A method according to claim 16, wherein the first wavelength is about 13 nm.
18. (Original) A method according to claim 12, wherein the first wavelength range is in a UV region.
19. (Original) A method according to claim 18, wherein the first wavelength is in a region between about 157 nm to 193 nm.
20. (Currently Amended) A method according to claim 12, further comprising using the second wavelength range for setup of a lithographic apparatus, the setup comprising ~~one or more of calibration, qualification, performance test, and alignment~~ (i) calibration, or (ii) qualification, or (iii) performance test, or (iv) alignment, or (v) any combination of (i)-(iv).
21. (Original) A method according to claim 12, further comprising using the first wavelength range for exposure of the substrate and using the second wavelength range for exposure of a further substrate.
22. (Currently Amended) A method according to claim ~~16~~12, wherein the second wavelength range is in a region between about 150 and 350 nm.
23. (New) A lithographic apparatus, comprising:

a radiation source configured to provide radiation to an illumination system, the radiation source configured to provide radiation in a first wavelength range and in a second wavelength range, the second wavelength range being different from the first wavelength range;

a support configured to support a patterning device, the patterning device configured to impart the radiation in the first wavelength range, or in the second wavelength range, or in both the first wavelength range and the second wavelength range, with a pattern in its cross-section;

a substrate table configured to hold a substrate;

a projection system configured to project the patterned radiation onto a target portion of the substrate,

wherein the lithographic apparatus is configured so that the first wavelength range is used in a controlled ambient environment in the lithographic apparatus, and the second wavelength range is used when the controlled ambient environment is not established.

24. (New) A lithographic apparatus according to claim 23, wherein the second wavelength range is used for setup of the lithographic apparatus, the setup comprising (i) calibration, or (ii) qualification, or (iii) performance test, or (iv) alignment, or (v) any combination of (i)-(iv).

25. (New) A lithographic apparatus according to claim 23, wherein the first wavelength range is in an EUV region.

26. (New) A lithographic apparatus according to claim 25, wherein the second wavelength range is in a region between about 150 and 350 nm.

27. (New) A lithographic apparatus according to claim 23, wherein the controlled ambient environment is a vacuum environment and the period when the controlled ambient environment is not established comprises establishing the vacuum environment.

28. (New) A device manufacturing method, comprising:
providing radiation at a first wavelength range and propagating the first wavelength range radiation in a controlled ambient environment;

providing radiation at a second wavelength range and propagating the second wavelength range radiation when the controlled ambient environment is not established, the second wavelength range being different from the first wavelength range;

patterning the radiation in the first wavelength range radiation, or the second wavelength range radiation, or both the first wavelength range radiation and the second wavelength range radiation, in its cross-section; and

projecting the patterned radiation onto a target portion of a substrate,

29. (New) A method according to claim 28, further comprising using the second wavelength range radiation for setup of a lithographic apparatus, the setup comprising (i) calibration, or (ii) qualification, or (iii) performance test, or (iv) alignment, or (v) any combination of (i)-(iv).

30. (New) A method according to claim 28, wherein the first wavelength range is in an EUV region.

31. (New) A method according to claim 30, wherein the second wavelength range is in a region between about 150 and 350 nm.

32. (New) A method according to claim 28, wherein the controlled ambient environment is a vacuum environment and the period when the controlled ambient environment is not established comprises establishing the vacuum environment.